

ATLAS Radiation Monitor

- ***integrating monitor***

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- Integrating part of the *ATLAS Radiation Monitor* will measure online:
 - Total Ionization Dose - TID
 - Non-Ionizing Energy Loss – (bulk damage in silicon)
 - Thermal Neutron Fluence (in the ID)

- more information in:
 - EDMS document: *ATL-IC-ES-0017*
 - http://www-f9.ijs.si/~mandic/RADMON/atlas_radiation_monitor.htm



Sensors for online radiation monitoring

Total Ionizing Dose (TID):

- RADFET's (threshold voltage increase)
 - thick oxide LAAS (for low doses), thin oxide REM (for high doses)

NIEL:

- PIN diodes under forward bias (resistivity increase with NIEL)
 - CMRP low fluences ($< 10^{12}$ n/cm²), BPW34F high fluences ($> 10^{12}$ n/cm²)
- EPI PIN-diodes (leakage current increase with NIEL)
 - Will be used only in the Inner Detector

Thermal neutrons (and monitor the damage of ABCD3T input transistor):

- DMILL bipolar transistor from ATMEL (increase of base current at given collector current)
 - Will be used only in the Inner Detector



Read-out

ELMB + ELMB DAC boards:

- ELMB available, 64 ADC channels
- DAC board (16 channels) produced and tested

Fully compatible with ATLAS DCS (CAN bus communication)

Compliant with radiation tolerance requirements

Readout principles

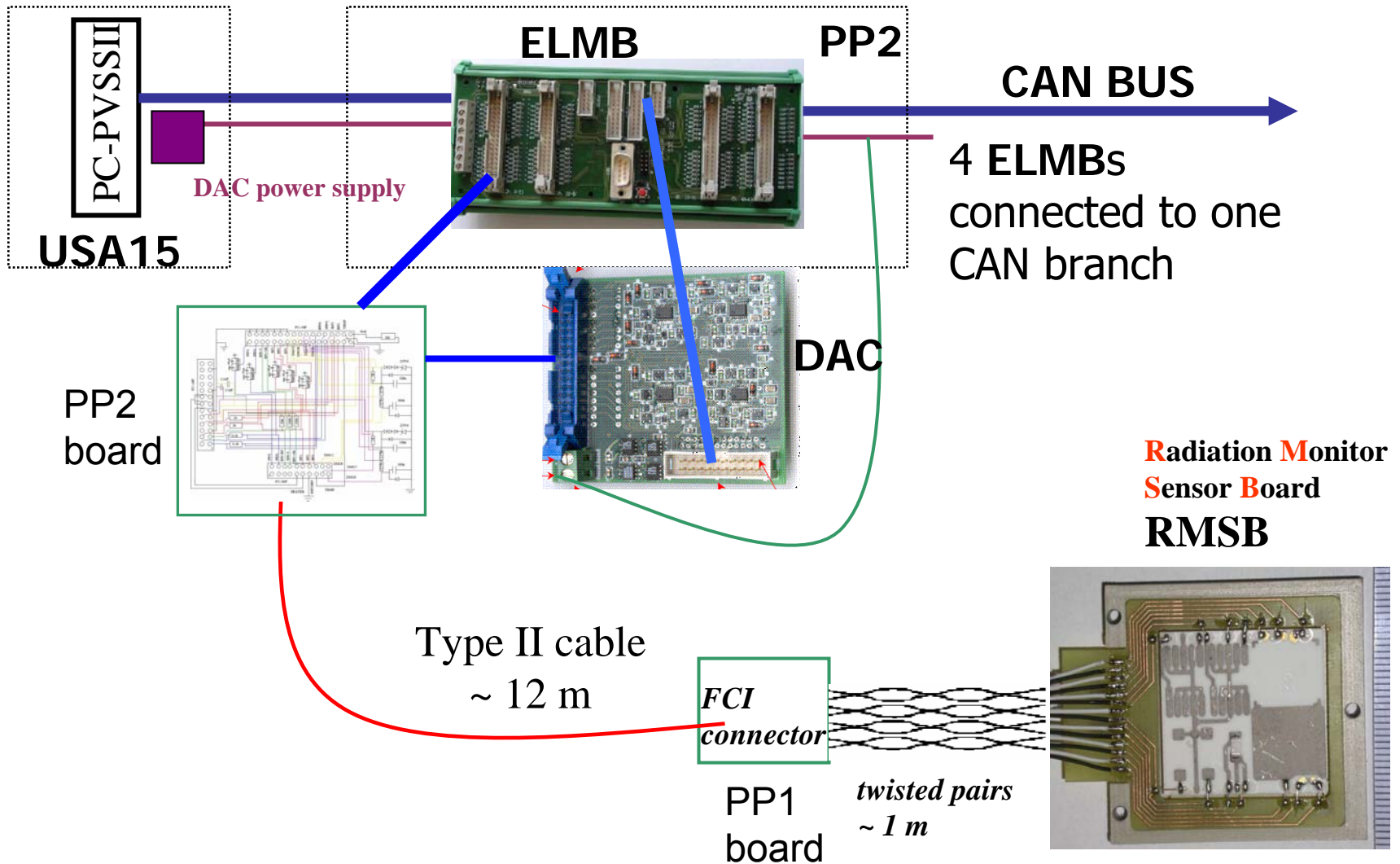
RADFET, PIN: current enforced (DAC)-voltage measured (ADC)

EPI: current (DAC) converted to voltage (resistor) –
voltage drop on resistor due to leakage current measured (ADC)

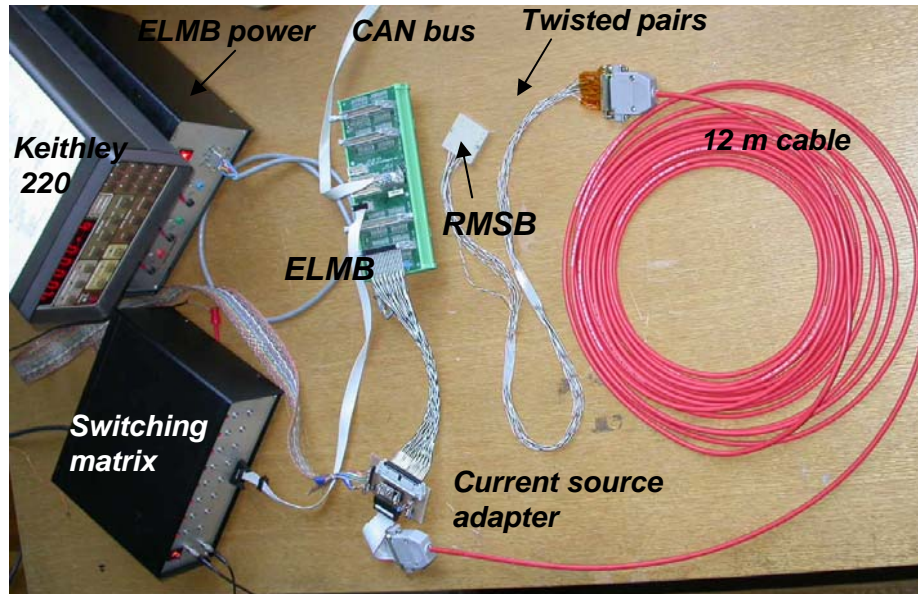
DMILL: collector current enforced (DAC) –
voltage drop on resistor due to base current measured (ADC)



Schematic view of the Inner Detector monitor



System test



Aim: determine the sensitivity of the system

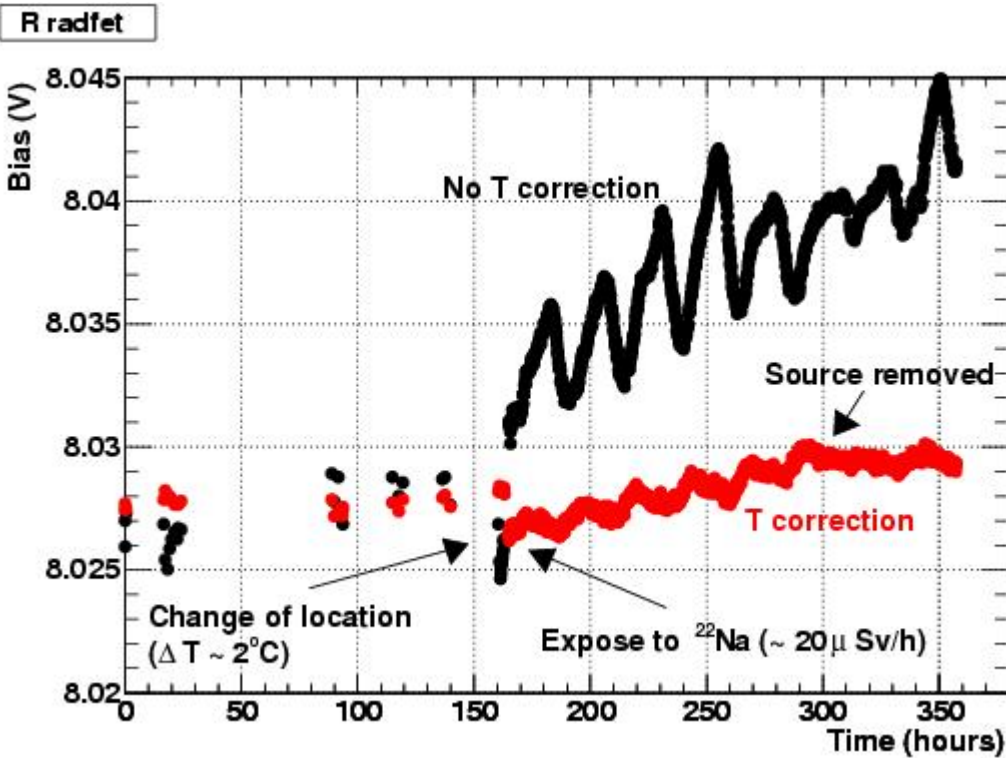
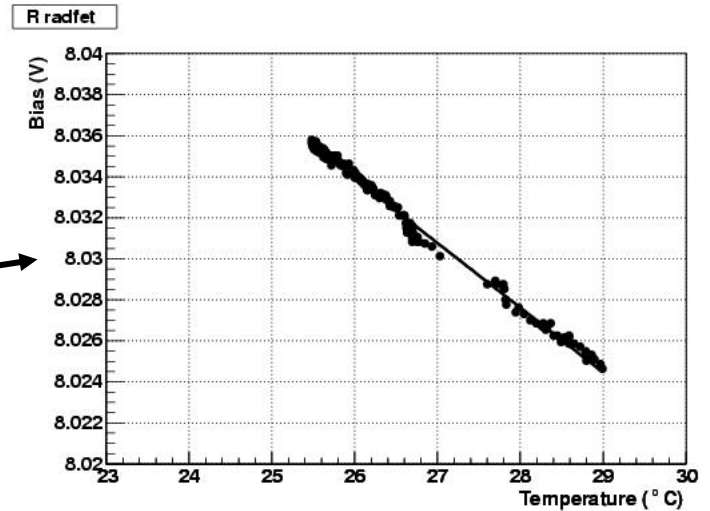
- read sensors in certain time intervals time
- after 150 hours RMSB exposed to ^{22}Na source ($D/t \sim 20 \mu\text{Sv/h}$)



REM thick oxide RADFET

Measure gate voltage at drain current $I_d = 160 \mu\text{A}$

Temperature of the RMSB not stabilized
→ correct for temperature variations offline



Detectable: $\Delta V \sim 2 \text{ mV}$

LAAS radfets ($\Delta V/\Delta D \sim 0.5 \text{ V/Gy}$):

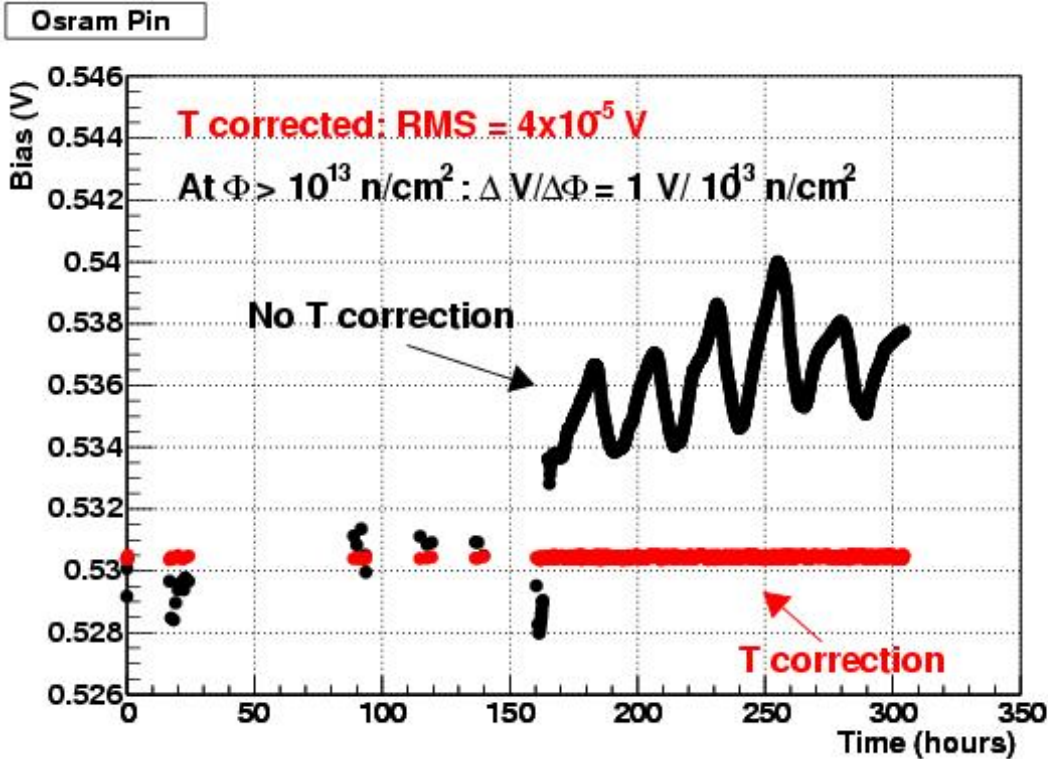
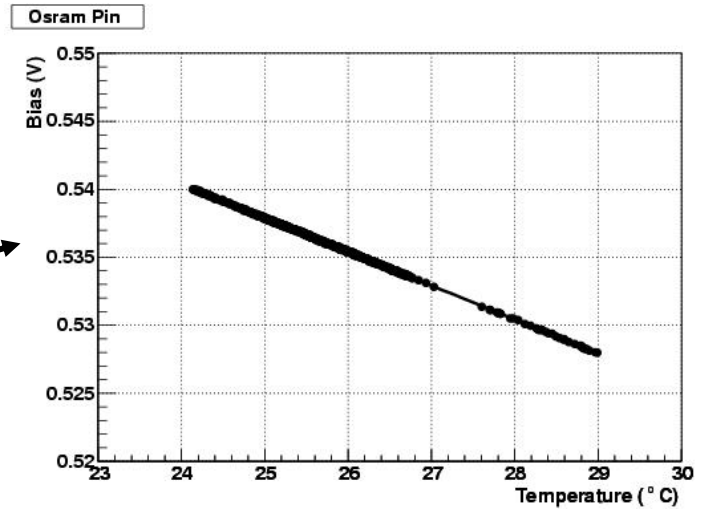
Sensitivity $\sim 4 \text{ mGy}$



Osram BPW34F pin diode

Measure bias voltage at forward current $I_f = 1 \text{ mA}$

Temperature of the RMSB not stabilized
→ correct for temperature variations offline:



Sensitivity:

BPW34F ($\Delta V / \Delta \Phi = 1 \text{ V} / 10^{13} \text{ n/cm}^2$)

→ better than 10^{10} n/cm^2
(but at $\Phi > 10^{10} \text{ n/cm}^2$)

CMRP ($\Delta V / \Delta \Phi = 1 \text{ V} / 10^{11} \text{ n/cm}^2$)

→ better than 10^8 n/cm^2



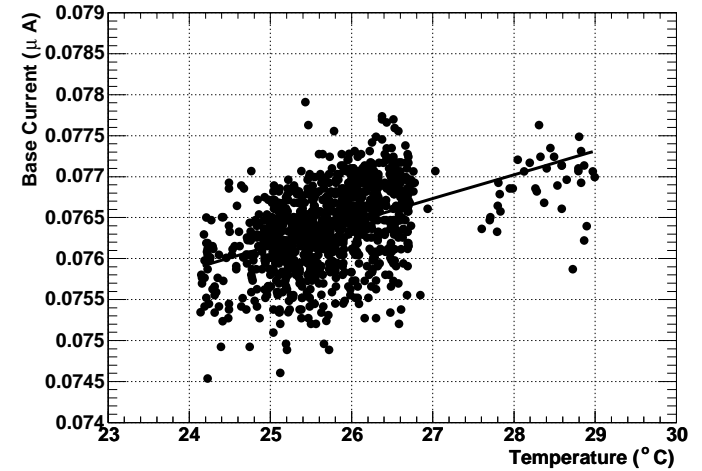
DMILL transistor:

Measure base current at collector current $I_c = 10 \mu\text{A}$

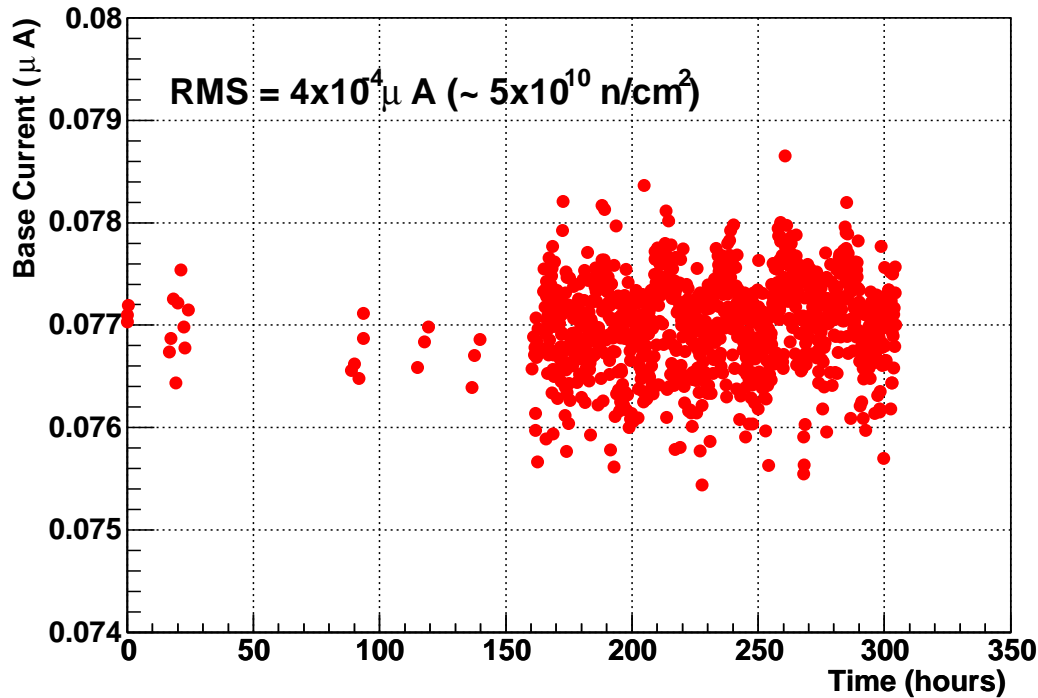
Temperature of the RMSB not stabilized
→ correct for temperature variations offline:



DMILL



Dmill Ib



Sensitivity:

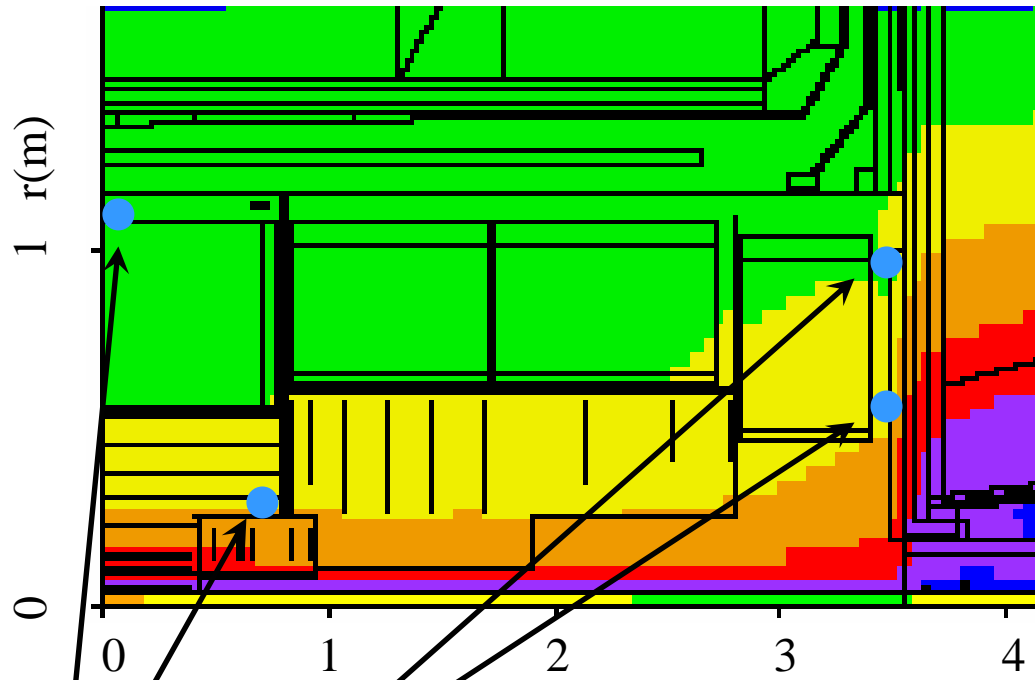
Can detect fluences higher than $\sim 5 \times 10^{10} \text{ n/cm}^2$



- Sensitivity: 4 mGy with LAAS radfets and 10^8 n/cm² with CMRP diodes is sufficient also for low luminosity years for most of subdetectors
- important to get early information to compare with simulations
- Inner Detector: need more sensors per location to cover larger range of doses and to have higher level of redundancy because of very limited access.



Positions of RMSBs in the ID



Side A ($z > 0$):
 at $\Phi = 0^\circ$ and 180°
 Side C ($z < 0$):
 at $\Phi = 90^\circ$ and 270°

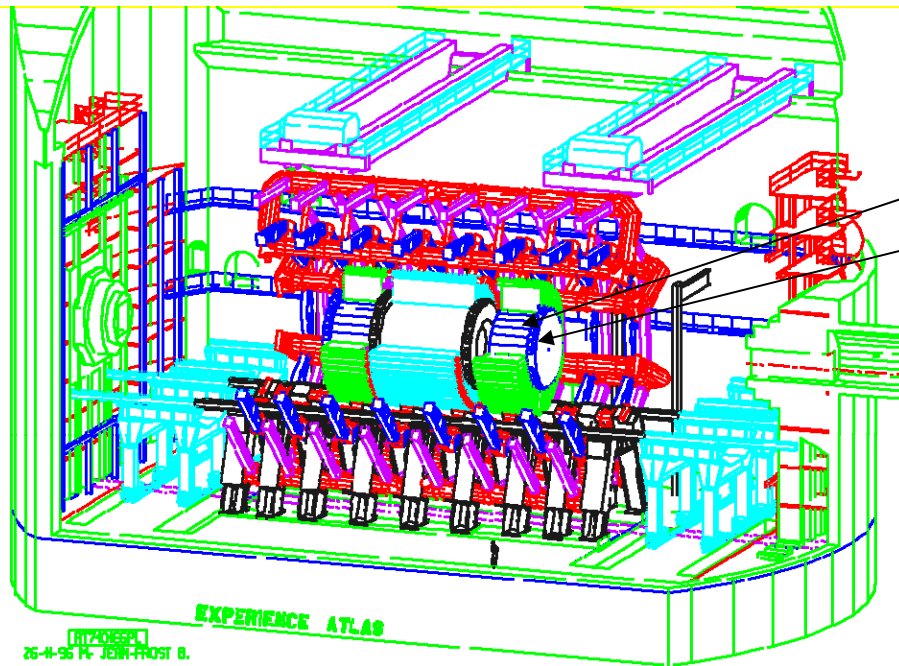
2 positions at
 $Z=0, R=110,$
 $\Phi = 0^\circ$ and 180°

Total of 14 in the ID

| $r[\text{cm}]$ | $z [\text{cm}]$ | Φ_{eq} [$10^{14}/\text{m}^2$] 10 y (LL y) | $\Phi(E > 20 \text{ MeV})$ [$10^{14}/\text{cm}^2$] | TID[10^4 Gy] 10 y (LL y) |
|----------------|-----------------|---|---|---|
| 20-30 | 80-90 | 2.33 (0.03) | 2.2 | 14 (0.2) |
| 40-50 | 340-350 | 2.35 (0.03) | 1.25 | 6.7 (0.09) |
| 80-90 | 340-350 | 1.06 (0.01) | 0.41 | 1.91 (0.03) |
| 100-110 | 0-10 | 0.51 (<0.01) | 0.15 | 0.76 (0.01) |



RMSBs in calorimeters



6 locations in Tiles
18 locations in LAr

LAAS radfets and CMRP diodes

| System | TID (Gy/10y) | TID (Gy/LL year) | ΔV in the first year (V) | ΔV (10y) | NIEL (n/cm ² /10y) | NIEL (n/cm ² /frist y) | ΔV first year (V) | ΔV (10y) |
|--------|--------------|------------------|----------------------------------|------------------|-------------------------------|-----------------------------------|---------------------------|------------------|
| Lar: | 5.7-50 | 0.08-0.7 | 0.04-0.3 | 2.-5. | 1.5e11-1.5e12 | 2.1e9-2.1e10 | 0.01-0.1 | 0.7-7 |
| TILE: | 0.2-2.5 | 0.003-0.035 | 0.002-0.02 | 0.1-1 | 1.5e10-2.3e11 | 2.1e8-3.2e9 | 0.002-0.02 | 0.08-1 |

- waiting for number of locations in muon detector



Software

- programming of processor on ELMB board:
 - sensor readout process controlled by ELMB (e.g.):
 - set DAC channel on
 - wait
 - read ADC channel
 - set DAC channel off
 - temperature stabilization of Inner Detector monitor boards controlled by ELMB
 - much simpler to use, less traffic on CAN BUS, less dependent on computer status



Status of monitor for Inner Detector:

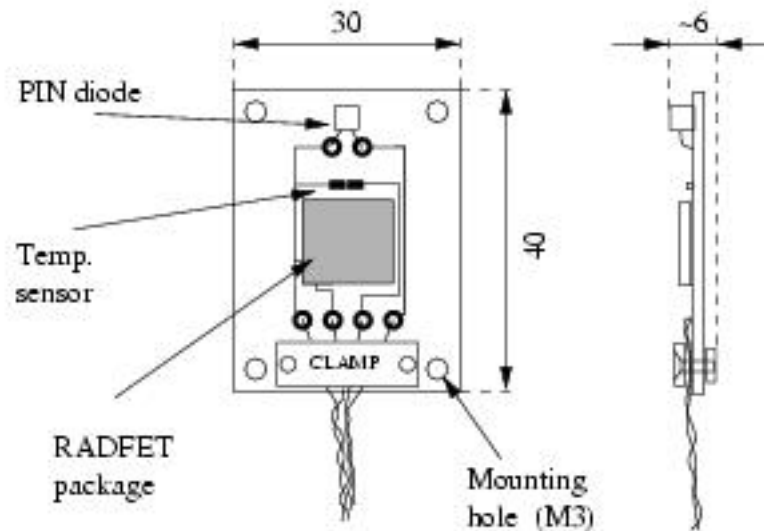
- prototype produced and tested
 - DACs, connection board, ceramic hybrid, housing designed and in production
 - cabling defined, space for patch panels and ELMBs reserved
 - software (programming of processor on ELMB board) written
 - sensors (RADFETs, CMRP, BPW34F) should be available soon
- whole system can be ready for installation by the end of the year



Status of Monitors for Locations Outside of the Inner Detector

- simplified version of ID system :

- LAAS radfet + CMRP diode + temperature sensor
- no temperature stabilization
- sensor board is a simple PCB
- can be delivered (board with pig-tail) soon after sensors are ready

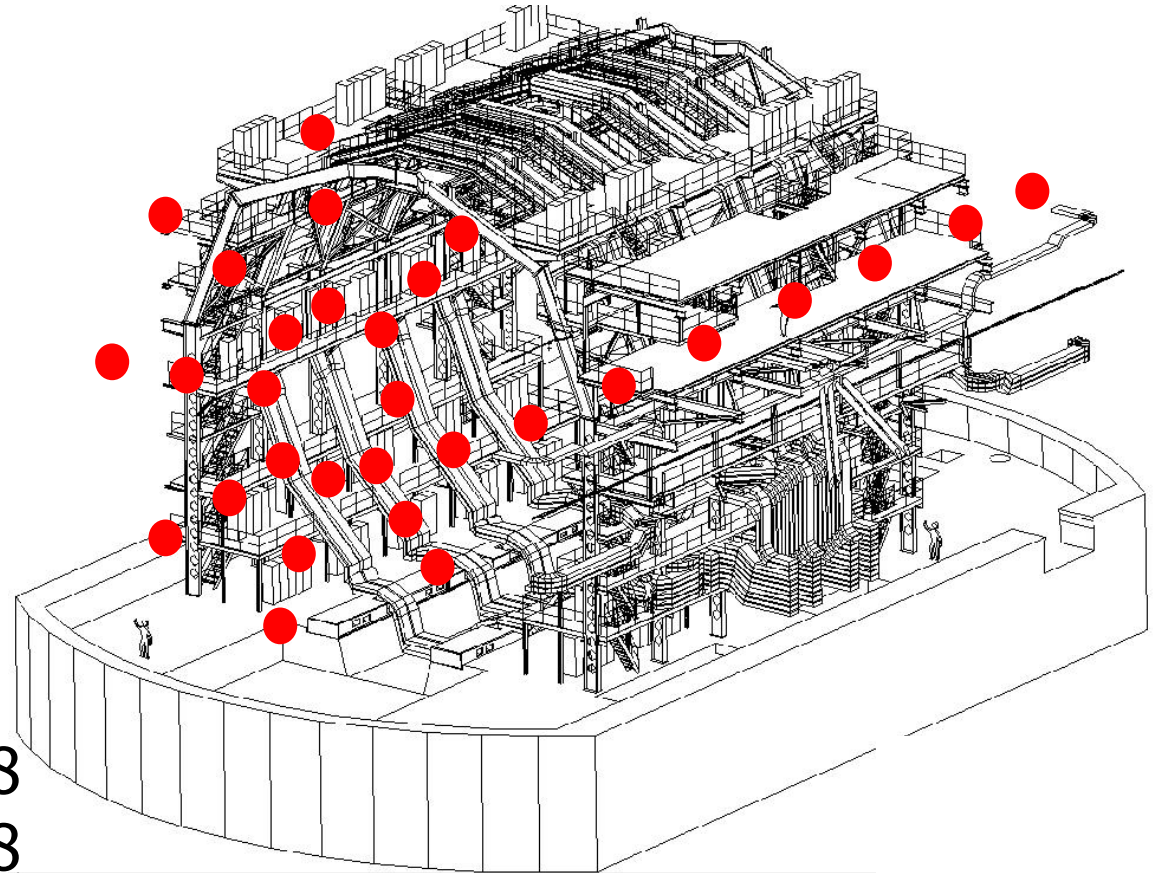


- waiting for number of locations in muon detector
- waiting for number of DAC boards needed by calorimeters



Proposal for locations of passive monitors (TLDs) made

- 154 racks
– All types



2 PHI planes with 3x8
5 PHI planes with 1x8
Total 88

F. Anfhinolfi, ATLAS RADMON meeting, 27/6/05

<http://agenda.cern.ch/fullAgenda.php?ida=a054176#2005-06-27>



New development by Muon System

M. Shupe, ATLAS RADMON meeting, 27/6/2005:

<http://agenda.cern.ch/fullAgenda.php?ida=a054176#2005-06-27>

- Measuring Atlas Radiation Backgrounds in the Muon System at Startup
- Monitor neutron, photon, and charged particle fluxes/spectra in pulsed mode for sensitivity at low luminosity. Compare measured fluxes to FLUKA and GCALOR to “recalibrate” simulations.



Conclusion

- radiation sensors selected, packaging defined
- prototypes made and tested
- all components for readout designed, production of components for Inner Detector started
- ELMB software written
- PCBs for sensor boards for Tile and LAr produced
- ➔ Waiting for information from Tile and LAr about cabling to start production of DAC and patch panel boards
- ➔ waiting for number of locations for muon subdetector system
- locations of passive dosimeters defined

